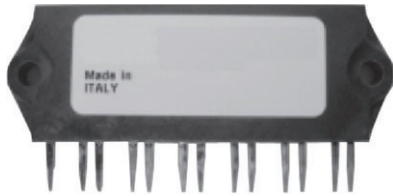


## IGBT SIP Module (Fast IGBT)



SIP (IMS-2)

PRIMARY CHARACTERISTICS	
OUTPUT CURRENT IN A TYPICAL 5.0 kHz MOTOR DRIVE	
$V_{CES}$	600 V
$I_{RMS}$ per phase (3.1 kW total) with $T_C = 90\text{ }^\circ\text{C}$	11 A
$T_J$	125 $^\circ\text{C}$
Supply voltage	360 $V_{DC}$
Power factor	0.8
Modulation depth See fig. 1	115 %
$V_{CE(on)}$ (typical) at $I_C = 4.8\text{ A}$ , 25 $^\circ\text{C}$	1.41 V
Speed	1 kHz to 8 kHz
Package	SIP
Circuit configuration	Three phase inverter

### FEATURES

- Fully isolated printed circuit board mount package
- Switching-loss rating includes all “tail” losses
- HEXFRED® soft ultrafast diodes
- Optimized for medium speed, see fig. 1 for current vs. frequency curve
- Designed and qualified for industrial level
- UL approved file E78996
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
COMPLIANT

### DESCRIPTION

The IGBT technology is the key to the advanced line of IMS (Insulated Metal Substrate) power modules. These modules are more efficient than comparable bipolar transistor modules, while at the same time having the simpler gate-drive requirements of the familiar power MOSFET. This superior technology has now been coupled to a state of the art materials system that maximizes power throughput with low thermal resistance. This package is highly suited to motor drive applications and where space is at a premium.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	$V_{CES}$		600	V
Continuous collector current, each IGBT	$I_C$	$T_C = 25\text{ }^\circ\text{C}$	8.8	A
		$T_C = 100\text{ }^\circ\text{C}$	4.8	
Pulsed collector current	$I_{CM}$	Repetitive rating; $V_{GE} = 20\text{ V}$ , pulse width limited by maximum junction temperature. See fig. 20	26	
Clamped inductive load current	$I_{LM}$	$V_{CC} = 80\%$ ( $V_{CES}$ ), $V_{GE} = 20\text{ V}$ , $L = 10\text{ }\mu\text{H}$ , $R_G = 50\text{ }\Omega$ See fig. 19	800	
Diode continuous forward current	$I_F$	$T_C = 100\text{ }^\circ\text{C}$	3.4	
Diode maximum forward current	$I_{FM}$		26	
Gate to emitter voltage	$V_{GE}$		$\pm 20$	V
Isolation voltage	$V_{ISOL}$	Any terminal to case, $t = 1\text{ min}$	2500	$V_{RMS}$
Maximum power dissipation, each IGBT	$P_D$	$T_C = 25\text{ }^\circ\text{C}$	23	W
		$T_C = 100\text{ }^\circ\text{C}$	9.1	
Operating junction and storage temperature range	$T_J, T_{Stg}$		-40 to +150	$^\circ\text{C}$
Soldering temperature		For 10 s	300 (0.063" (1.6 mm) from case)	
Mounting torque		6-32 or M3 screw	5 to 7 (0.55 to 0.8)	lbf · in (N · m)

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TYP.	MAX.	UNITS
Junction to case, each IGBT, one IGBT in conduction	$R_{thJC}$ (IGBT)	-	5.5	$^\circ\text{C/W}$
Junction to case, each diode, one diode in conduction	$R_{thJC}$ (diode)	-	9.0	
Case to sink, flat, greased surface	$R_{thCS}$ (module)	0.1	-	
Weight of module		20 (0.7)	-	g (oz.)



<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{ V}$ , $I_C = 250\text{ }\mu\text{A}$ Pulse width $\leq 80\text{ }\mu\text{s}$ , duty factor $\leq 0.1\%$	600	-	-	V
Temperature coeff. of breakdown voltage	$\Delta V_{(BR)CES} / \Delta T_J$	$V_{GE} = 0\text{ V}$ , $I_C = 1.0\text{ mA}$	-	0.72	-	V/ $^\circ\text{C}$
Collector to emitter saturation voltage	$V_{CE(on)}$	$I_C = 4.8\text{ A}$	-	1.41	1.7	V
		$I_C = 8.8\text{ A}$				
		$I_C = 4.8\text{ A}$ , $T_J = 150\text{ }^\circ\text{C}$				
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$ , $I_C = 250\text{ }\mu\text{A}$	3.0	-	6.0	
Gate to emitter leakage current	$I_{GES}$	$V_{GE} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
Temperature coeff. of threshold voltage	$\Delta V_{GE(th)} / \Delta T_J$	$V_{GE} = 0\text{ V}$ , $I_C = 1.0\text{ mA}$	-	-11	-	mV/ $^\circ\text{C}$
Forward transconductance	$g_{fe}$	$V_{CE} = 100\text{ V}$ , $I_C = 4.8\text{ A}$ Pulse width $5.0\text{ }\mu\text{s}$ ; single shot	2.9	5.0	-	S
Zero gate voltage collector current	$I_{CES}$	$V_{GE} = 0\text{ V}$ , $V_{CE} = 600\text{ V}$	-	-	250	$\mu\text{A}$
		$V_{GE} = 0\text{ V}$ , $V_{CE} = 600\text{ V}$ , $T_J = 150\text{ }^\circ\text{C}$	-	-	1700	
Diode forward voltage drop	$V_{FM}$	$I_C = 8.0\text{ A}$	-	1.4	1.7	V
		$I_C = 8.0\text{ A}$ , $T_J = 150\text{ }^\circ\text{C}$				
		See fig. 13	-	1.3	1.6	

<b>SWITCHING CHARACTERISTICS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Total gate charge (turn on)	$Q_g$	$I_C = 4.8\text{ A}$ $V_{CC} = 400\text{ V}$ See fig. 8	-	30	45	nC
Gate to emitter charge (turn on)	$Q_{ge}$		-	4.0	6.0	
Gate to collector charge	$Q_{gc}$		-	13	20	
Turn-on delay time	$t_{d(on)}$	$T_J = 25\text{ }^\circ\text{C}$ $I_C = 4.8\text{ A}$ , $V_{CC} = 480\text{ V}$ $V_{GE} = 15\text{ V}$ , $R_G = 50\text{ }\Omega$ Energy losses include "tail" and diode reverse recovery. See fig. 9, 10, 18	-	49	-	ns
Rise time	$t_r$		-	22	-	
Turn-off delay time	$t_{d(off)}$		-	200	300	
Fall time	$t_f$		-	214	320	mJ
Turn-on switching loss	$E_{on}$		-	0.23	-	
Turn-off switching loss	$E_{off}$		-	0.33	-	
Total switching loss	$E_{ts}$	-	0.45	0.70		
Turn-on delay time	$t_{d(on)}$	$T_J = 150\text{ }^\circ\text{C}$ , $I_C = 4.8\text{ A}$ , $V_{CC} = 480\text{ V}$ $V_{GE} = 15\text{ V}$ , $R_G = 50\text{ }\Omega$ Energy losses include "tail" and diode reverse recovery See fig. 10, 11, 18	-	48	-	ns
Rise time	$t_r$		-	25	-	
Turn-off delay time	$t_{d(off)}$		-	435	-	
Fall time	$t_f$		-	364	-	mJ
Total switching loss	$E_{ts}$		-	0.93	-	
			-			
Input capacitance	$C_{ies}$	$V_{GE} = 0\text{ V}$ $V_{CC} = 30\text{ V}$	-	340	-	pF
Output capacitance	$C_{oes}$					
Reverse transfer capacitance	$C_{res}$					
Diode reverse recovery time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}$	-	37	55	ns
		$T_J = 125\text{ }^\circ\text{C}$				
Diode peak reverse recovery current	$I_{rr}$	$T_J = 25\text{ }^\circ\text{C}$	-	3.5	50	A
		$T_J = 125\text{ }^\circ\text{C}$				
Diode reverse recovery charge	$Q_{rr}$	$T_J = 25\text{ }^\circ\text{C}$	-	65	138	nC
		$T_J = 125\text{ }^\circ\text{C}$				
Diode peak rate of fall of recovery during $t_b$	$dl_{(rec)M} / dt$	$T_J = 25\text{ }^\circ\text{C}$	-	240	-	A/ $\mu\text{s}$
		$T_J = 125\text{ }^\circ\text{C}$				

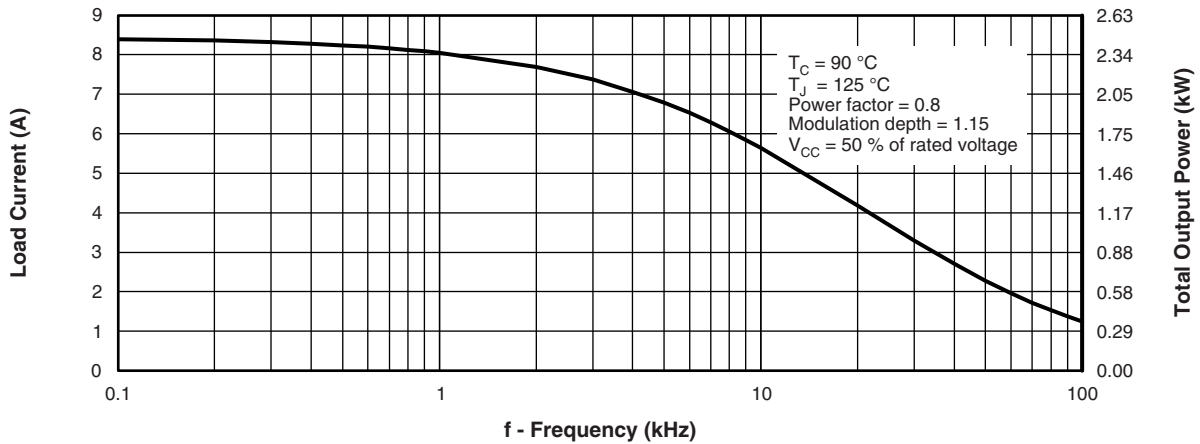


Fig. 1 - Typical Load Current vs. Frequency  
(Load Current =  $I_{RMS}$  of Fundamental)

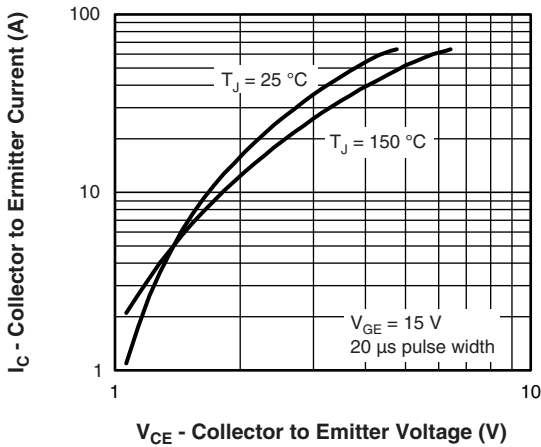


Fig. 2 - Typical Output Characteristics

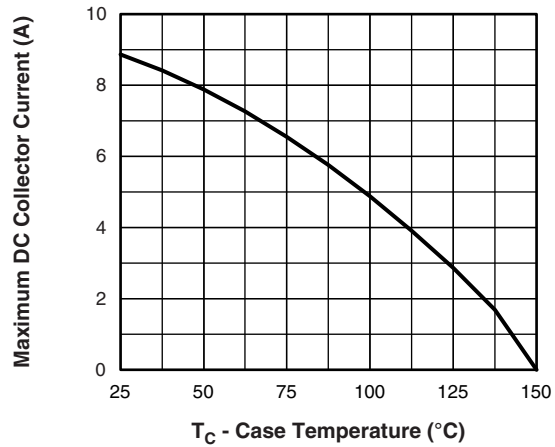


Fig. 4 - Maximum Collector Current vs. Case Temperature

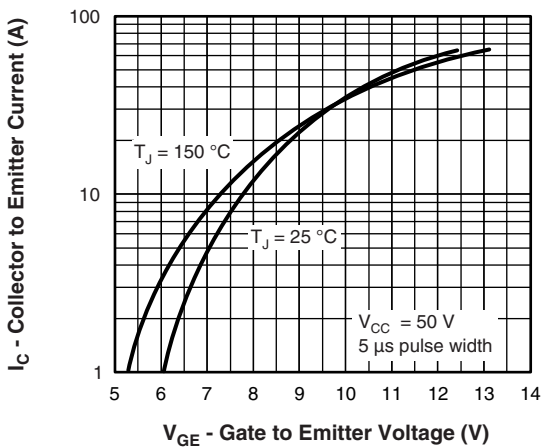


Fig. 3 - Typical Transfer Characteristics

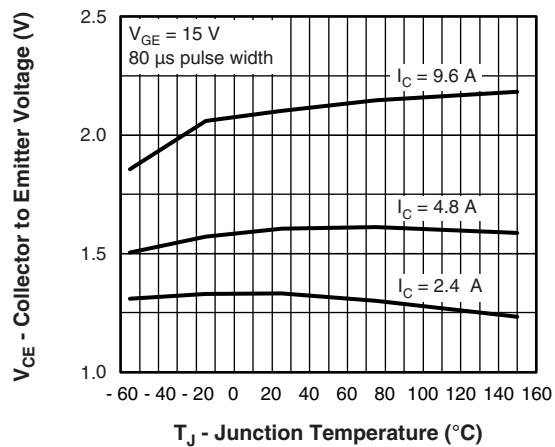


Fig. 5 - Typical Collector to Emitter Voltage vs. Junction Temperature

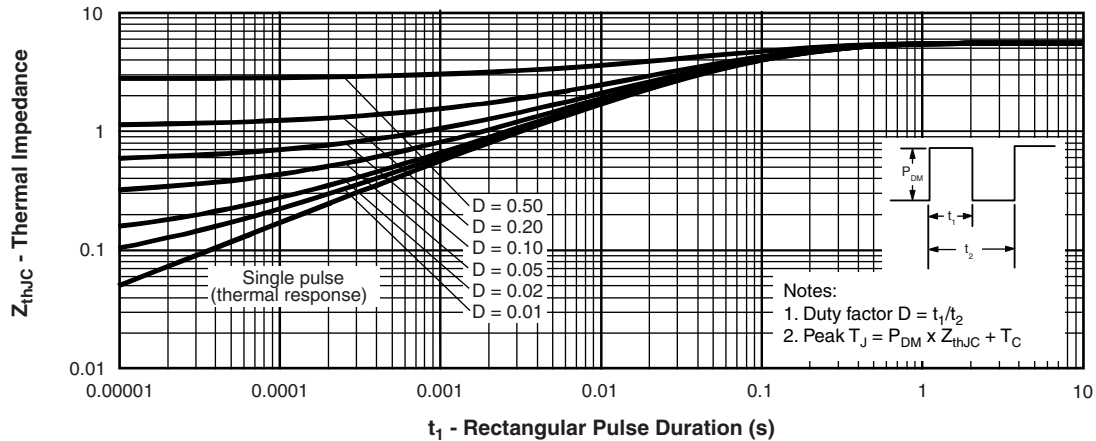


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction to Case

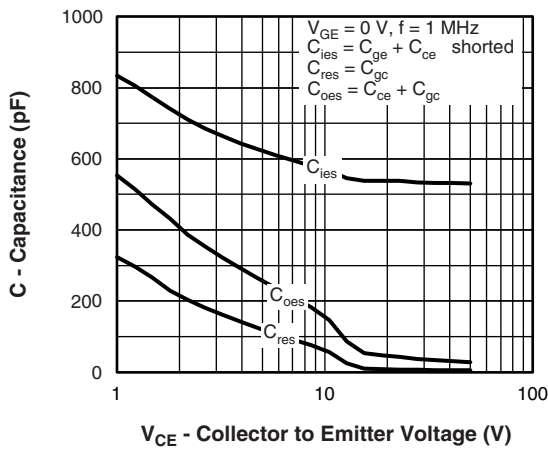


Fig. 7 - Typical Capacitance vs. Collector to Emitter Voltage

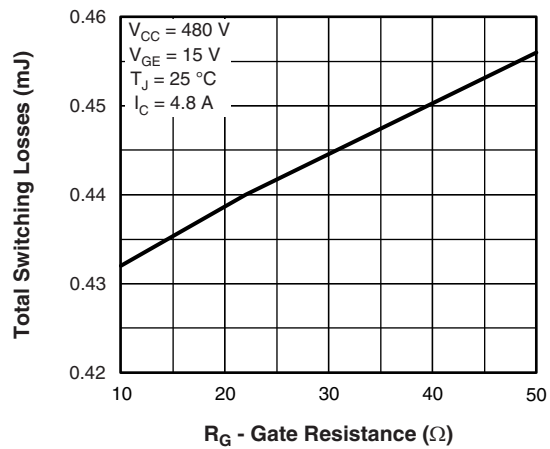


Fig. 9 - Typical Switching Losses vs. Gate Resistance

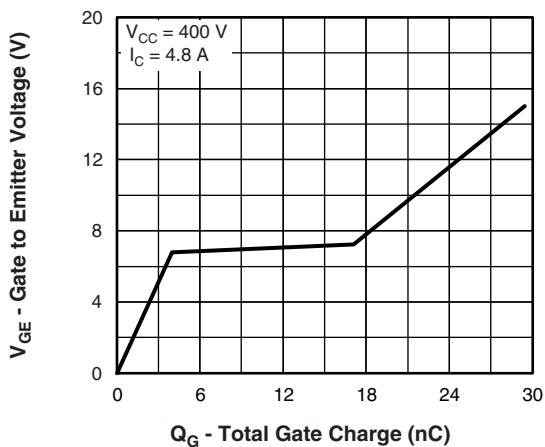


Fig. 8 - Typical Gate Charge vs. Gate to Emitter Voltage

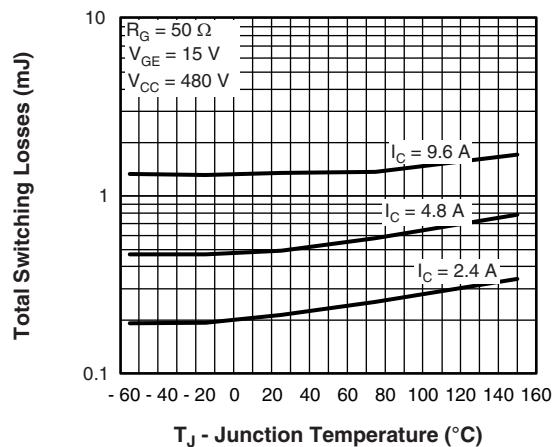


Fig. 10 - Typical Switching Losses vs. Junction Temperature

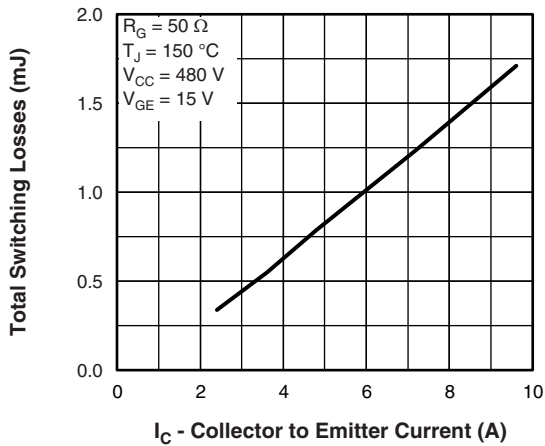


Fig. 11 - Typical Switching Losses vs. Collector to Emitter Current

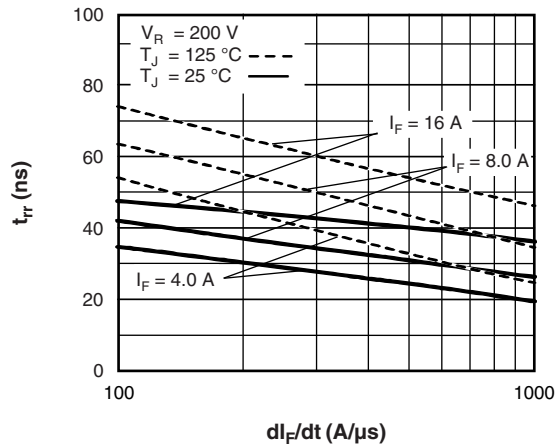


Fig. 14 - Typical Reverse Recovery Time vs.  $di_F/dt$

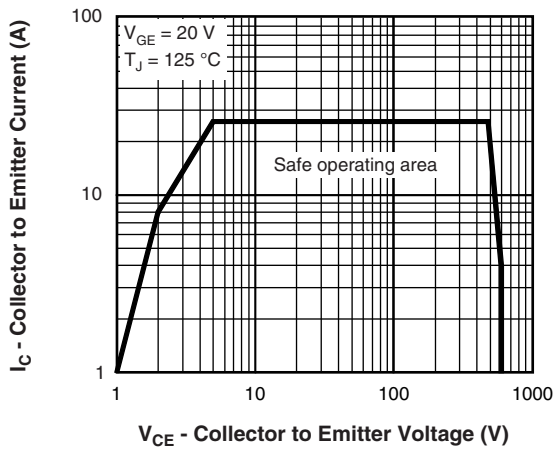


Fig. 12 - Turn-Off SOA

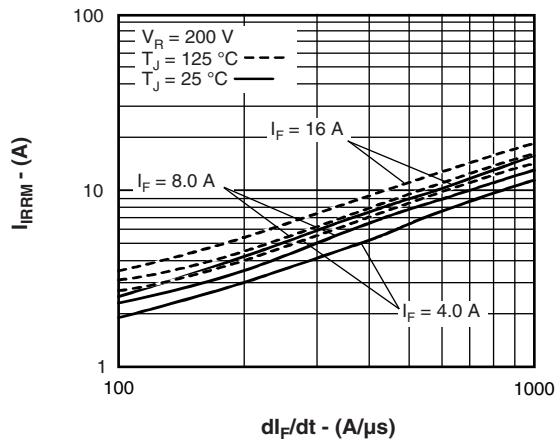


Fig. 15 - Typical Recovery Current vs.  $di_F/dt$

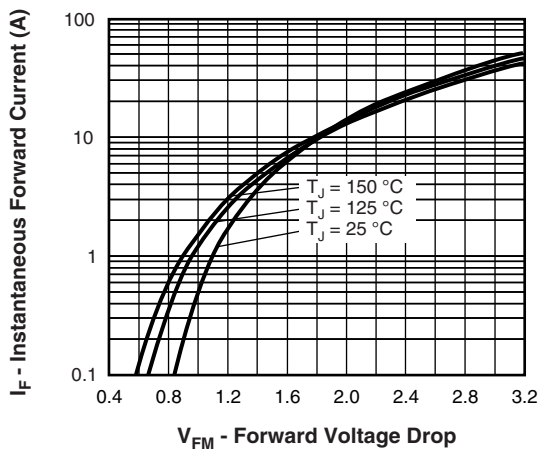


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

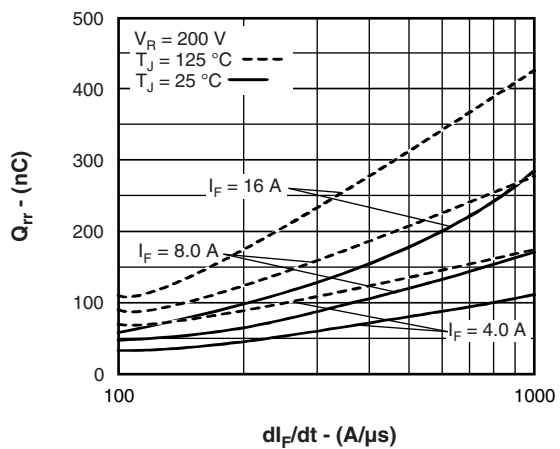


Fig. 16 - Typical Stored Charge vs.  $di_F/dt$

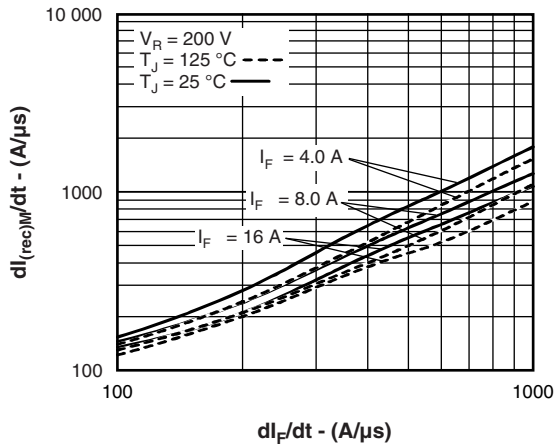


Fig. 17 - Typical  $dI_{(REC)M}/dt$  vs  $dI_F/dt$

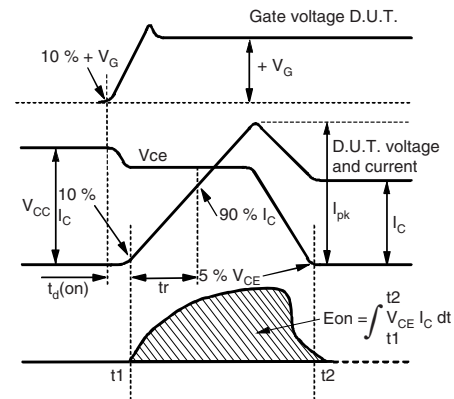


Fig. 18c - Test Waveforms of Circuit of Fig. 18a, Defining  $E_{on}$ ,  $t_{d(on)}$ ,  $t_r$

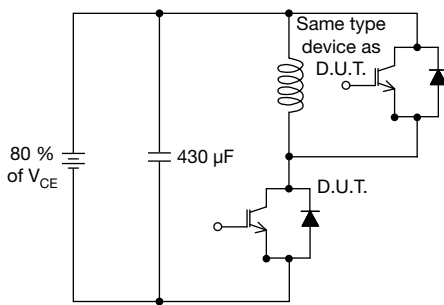


Fig. 18a - Test Circuit for Measurement of  $I_{LM}$ ,  $E_{on}$ ,  $E_{off(diode)}$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$ ,  $t_{d(on)}$ ,  $t_r$ ,  $t_{d(off)}$ ,  $t_f$

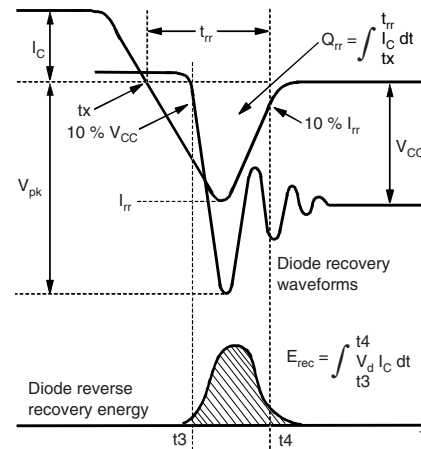


Fig. 18d - Test Waveforms of Circuit of Fig. 18a, Defining  $E_{rec}$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$

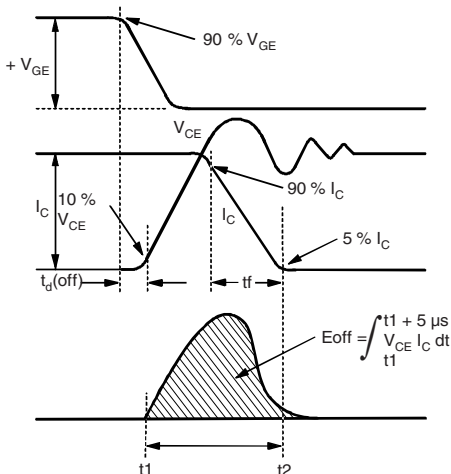


Fig. 18b - Test Waveforms of Circuit of Fig. 18a, Defining  $E_{off}$ ,  $t_{d(off)}$ ,  $t_f$

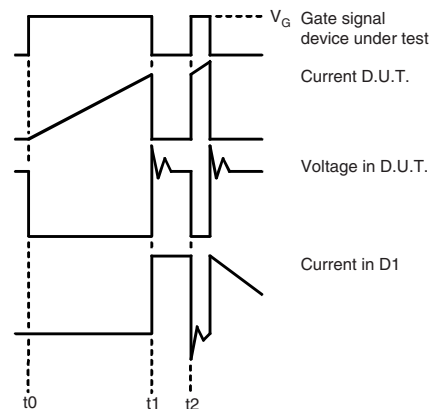


Fig. 18e - Macro Waveforms for Figure 18a's Test Circuit

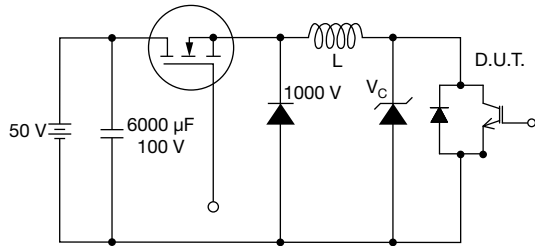


Fig. 19 - Clamped Inductive Load Test Circuit

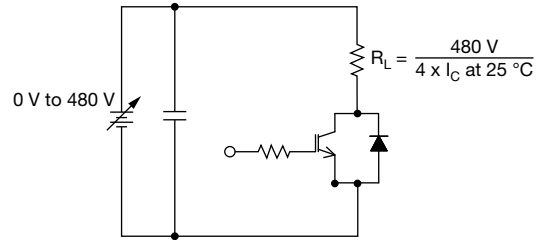
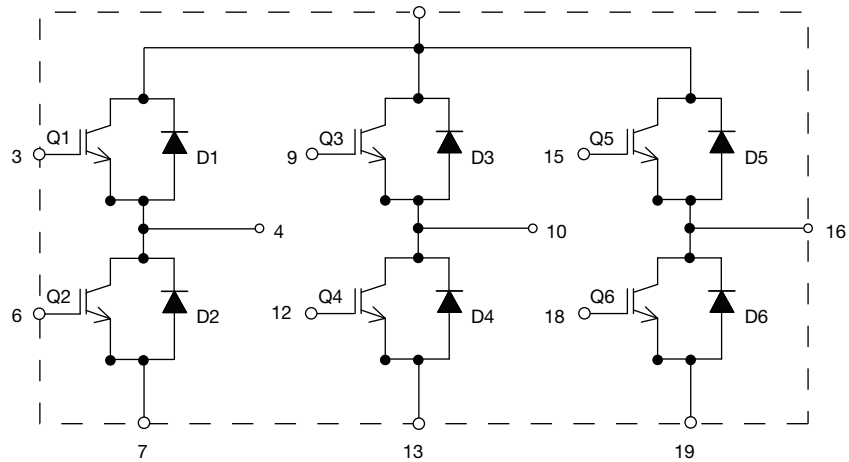


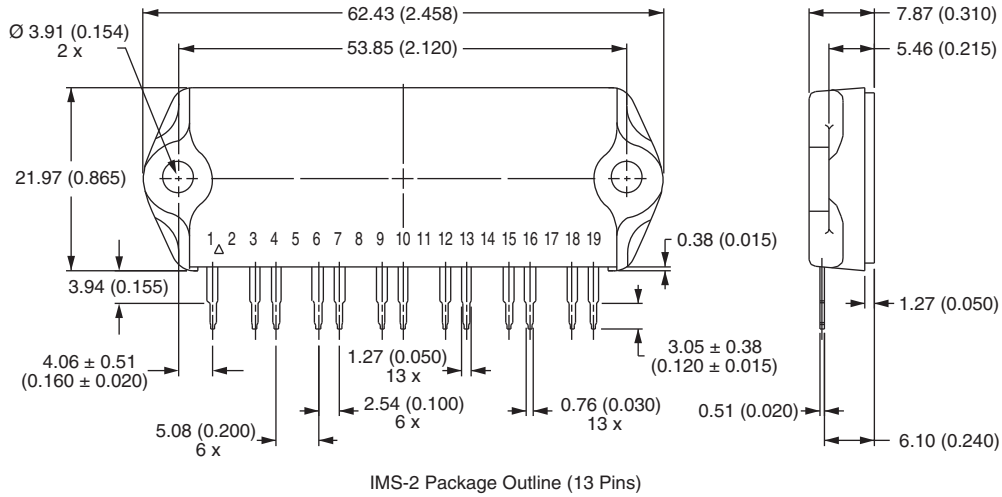
Fig. 20 - Pulsed Collector Current Test Circuit

**CIRCUIT CONFIGURATION**

**LINKS TO RELATED DOCUMENTS**

Dimensions	<a href="http://www.vishay.com/doc?95066">www.vishay.com/doc?95066</a>
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## IMS-2 (SIP)

**DIMENSIONS** in millimeters (inches)



### Notes

- (1) Tolerance unless otherwise specified  $\pm 0.254$  mm (0.010")
- (2) Controlling dimension: inch
- (3) Terminal numbers are shown for reference only





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